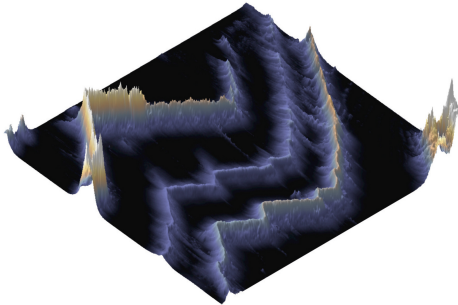




Lukas Raimund Puntigam (Autor)  
**Emergent and artificial conductive mesoscale  
patterns in a polar Mott insulator**

Lukas R. Puntigam

Emergent and Artificial Conductive  
Mesoscale Patterns in a Polar Mott  
Insulator



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